

.025" NPN Phototransistors

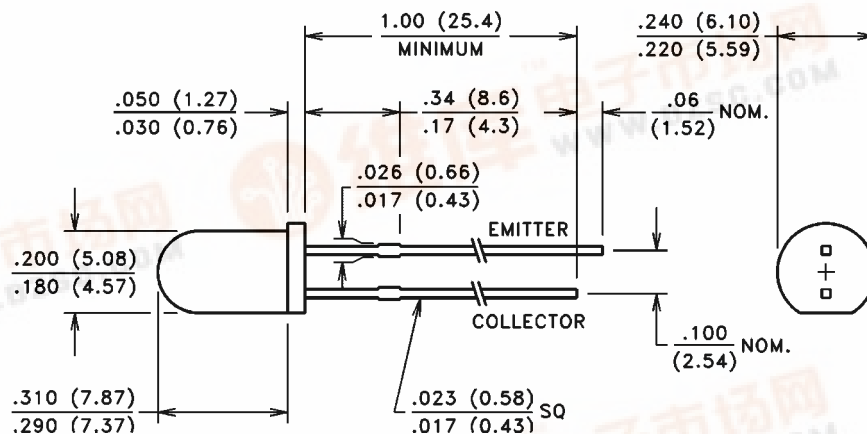
Clear T-1 $\frac{3}{4}$ (5 mm) Plastic Package

捷多邦, 专业PCB打样工厂, 24小时加急出货

VTT1225, 26, 27



PACKAGE DIMENSIONS inch (mm)



CASE 26 T-1 $\frac{3}{4}$ (5 mm)
CHIP TYPE: 25T

PRODUCT DESCRIPTION

A small area high speed NPN silicon phototransistor mounted in a 5 mm diameter lensed, end looking, transparent plastic package. Detectors in this series have a half power acceptance angle ($\theta_{1/2}$) of 5°. These devices are spectrally and mechanically matched to the VTE12xx series of IREDs.

ABSOLUTE MAXIMUM RATINGS ■

(@ 25°C unless otherwise noted)

Maximum Temperatures	
Storage Temperature:	-40°C to 100°C
Operating Temperature:	-40°C to 100°C
Continuous Power Dissipation:	50 mW
Derate above 30°C:	0.71 mW/°C
Maximum Current:	25 mA
Lead Soldering Temperature:	260°C
(1.6 mm from case, 5 sec. max.)	

ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also typical curves, pages 91-92)

Part Number ■	Light Current			Dark Current		Collector Breakdown	Emitter Breakdown	Saturation Voltage	Rise/Fall Time	Angular Response θ _{1/2}
	I _C			I _{CEO}		V _{BR(CEO)}	V _{BR(ECO)}	V _{CE(SAT)}	t _R /t _F	
	mA		H f _C (mW/cm ²) V _{CE} = 5.0 V	H = 0		I _C = 100 μA H = 0	I _E = 100 μA H = 0	I _C = 1.0 mA H = 400 f _C	I _C = 1.0 mA R _L = 100 Ω	
	Min.	Max.		(nA) Max.	V _{CE} (Volts)	Volts, Min.	Volts, Min.	Volts, Max.	μsec, Typ.	Typ.
VTT1225	4.0	—	100 (5)	100	10	30	5.0	0.25	1.5	±5°
VTT1226	7.5	—	100 (5)	100	10	30	5.0	0.25	3.0	±5°
VTT1227	12.0	—	100 (5)	100	10	30	5.0	0.25	4.0	±5°

Refer to General Product Notes, page 2.

